TECHNICAL DATA DATA SHEET 5088, REV A.1

Small Signal Switching Diode Die

FEATURES / BENEFITS:

- ✓ Die fabricated on a MIL-PRF-19500 manufacturing line
- ✓ Class H and Class K element evaluation available
- ✓ All ratings are @ T_A = 25 °C unless otherwise specified

ELECTRICAL CHARACTERISTICS:

MAXIMUM RATINGS

ALL RATINGS ARE AT TA = 25 °C UNLESS OTHERWISE SPECIFIED

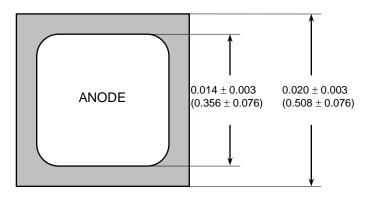
RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	150	V (pk)
WORKING PEAK REVERSE VOLTAGE	V_{RWM}	125	V (pk)
MAXIMUM AVERAGE DC OUTPUT CURRENT	Io	150	mA dc
PEAK SINGLE CYCLE SURGE CURRENT (t _p = 1 s, half sine wave)	I _{FSM}	0.5	A (pk)
$(t_p = 1 \mu s, , half sine wave)$		4.0	
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	T _{op, stg}	-65 to +175	°C

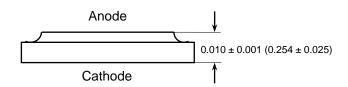
ELECTRICAL CHARACTERISTICS

ELECTRICAL CHARACTERIST	100				
CHARACTERISTIC		SYMBOL	MIN.	MAX.	UNITS
FORWARD VOLTAGE DROP	$(I_F = 200 \text{ mA dc})$	V _{F1}	0.83	1.00	
	$(I_F = 100 \text{ mA dc})$	V_{F2}	0.79	0.92	
	$(I_F = 50 \text{ mA dc})$	V_{F3}	0.74	0.88	\/ do
	$(I_F = 10 \text{ mA dc})$	V_{F4}	0.65	0.80	V dc
	$(I_F = 5 \text{ mA dc})$	V_{F5}	0.60	0.765	
	$(I_F = 1 \text{ mA dc})$	V_{F6}	0.52	0.70	
REVERSE CURRENT	$(V_R = 125 \text{ V dc})$	I _{R1}	-	0.001	μA dc
	$(V_R = 125 \text{ V dc}, T_A = 150^{\circ}\text{C})$	I _{R2}	-	3.0	
REVERSE RECOVERY TIME	$(I_F = 10 \text{ mA dc}, V_R = 35 \text{V dc})$	t _{rr}	-	3.0	μS
JUNCTION CAPACITANCE	$(f = 1MHz, V_{sig} = 50mV p-p, V_R = 0V dc)$	C _{JMAX}	-	8.0	pF

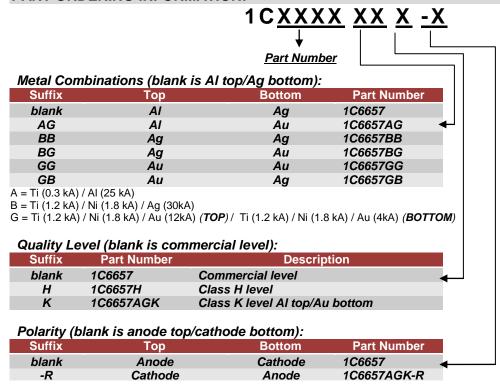
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PACKAGE DIMENSIONS (inches/mm):





PART ORDERING INFORMATION:





1C3595
SMALL SIGNAL SWITCHING DIODE DIE

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